30V PNP LOW SATURATION MEDIUM POWER TRANSISTOR IN SOT89

SUMMARY

 BV_{CEO} = -30V : R_{SAT} = 24m Ω ; I_{C} = -5.5A

DESCRIPTION

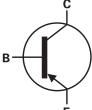
Packaged in the SOT89 outline this new low saturation 30V PNP transistor offers low on state losses making it ideal for use in DC-DC circuits, line switching and various driving and power management functions.



SOT89

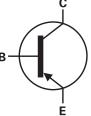
FEATURES

- 5.5 amps continuous current
- Up to 20 amps peak current
- · Very low saturation voltages
- Exceptional gain linearity down to 10mA
- Excellent high current gain hold up



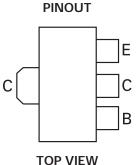
APPLICATIONS

- DC DC converters
- MOSFET gate drivers
- · Charging circuits
- · Power switches
- Motor control



ORDERING INFORMATION

DEVICE	REEL SIZE	TAPE WIDTH	QUANTITY PER REEL	
ZXTP2008ZTA	7"	12mm embossed	1000 units	



DEVICE MARKING

949

ISSUE 1 - JUNE 2005

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Collector-base voltage	BV _{CBO}	-50	V
Collector-emitter voltage	BV _{CEO}	-30	V
Emitter-base voltage	BV _{EBO}	-7	V
Continuous collector current ^(a)	I _C	-5.5	А
Peak pulse current	I _{CM}	-20	А
Power dissipation at T _A =25°C ^(a)	P _D	1.5	W
Linear derating factor		12	mW/°C
Power dissipation at T _A =25°C ^(b)	P _D	2.1	W
Linear derating factor		16.8	mW/°C
Operating and storage temperature range	T _j , T _{stg}	-55 to 150	°C

THERMAL RESISTANCE

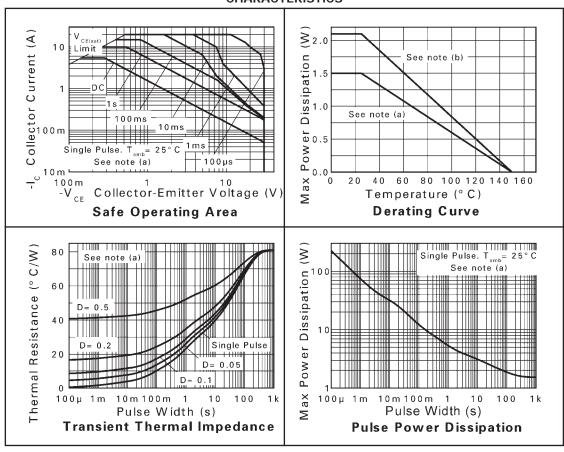
PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient ^(a)	$R_{\Theta JA}$	83	°C/W
Junction to Ambient ^(b)	$R_{\Theta JA}$	60	°C/W

NOTES

(a) For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

⁽b) For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

CHARACTERISTICS

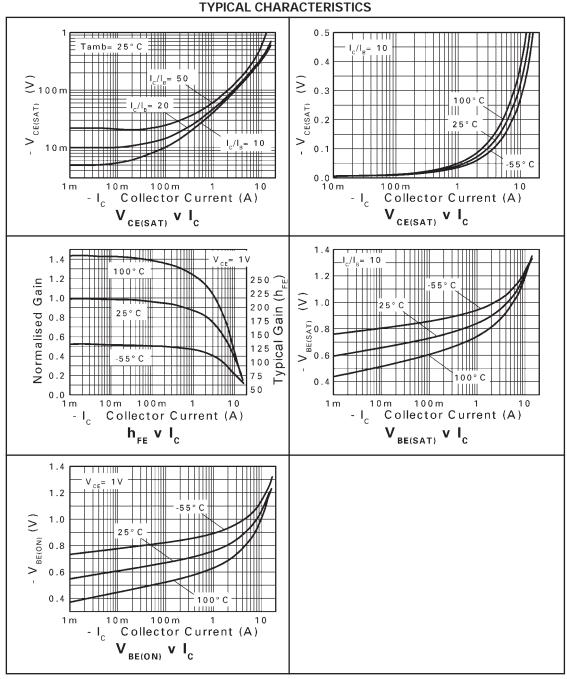


ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C unless otherwise stated)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS
Collector-base breakdown voltage	BV _{CBO}	-50	-70		V	I _C = -100μA
Collector-emitter breakdown voltage	BV _{CER}	-50	-70		V	$I_C = -1\mu A$, RB < $1k\Omega$
Collector-emitter breakdown voltage	BV _{CEO}	-30	-40		V	I _C = -10mA *
Emitter-base breakdown voltage	BV _{EBO}	-7.0	-8.0		V	I _E = -100μA
Collector cut-off current	I _{CBO}		<-1	-20	nA	V _{CB} = -40V
				-0.5	μΑ	$V_{CB} = -40V, T_{amb} = 100^{\circ}C$
Collector cut-off current	I _{CER}		<-1	-20	nA	V _{CB} = -40V
	R <1kΩ			-0.5	μΑ	$V_{CB} = -40V, T_{amb} = 100^{\circ}C$
Emitter cut-off current	I _{EBO}		<-1	-10	nA	V _{EB} = -6V
Collector-emitter saturation voltage	V _{CE(SAT)}		-25	-40	mV	I _C = -0.5A, I _B = -20mA *
			-35	-55	mV	I _C = -1A, I _B = -100mA *
			-55	-80	mV	I _C = -1A, I _B = -20mA *
			-55	-80	mV	I _C = -2A, I _B = -200mA *
			-130	-175	mV	I _C = -5.5A, I _B =-500mA *
Base-emitter saturation voltage	V _{BE(SAT)}		-970	-1070	mV	I _C = -5.5A, I _B = -500mA *
Base-emitter turn-on voltage	V _{BE(ON)}		-860	-960	mV	I _C = -5.5A, V _{CE} = -1V *
Static forward current transfer ratio	h _{FE}	100	225			I _C = -10mA, V _{CE} = -1V *
		100	200	300		I _C = -1A, V _{CE} = -1V *
		70	145			I _C = -5A, V _{CE} = -1V *
		10	20			I _C = -20A, V _{CE} = -1V *
Transition frequency	f _T		110		MHz	I _C = -100mA, V _{CE} = -10V
						f = 50MHz
Output capacitance	C _{OBO}		83		pF	V _{CB} = -10V, f = 1MHz *
Switching times	t _{ON}		43		ns	I _C = -1A, V _{CC} = -10V,
	t _{OFF}		230			$I_{B1} = -I_{B2} = -100 \text{mA}$

NOTES

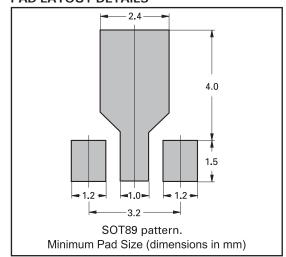
^{*} Measured under pulsed conditions. Pulse width $\leq 300 \mu s;$ duty cycle $\leq 2\%.$



ISSUE 1 - JUNE 2005

PACKAGE OUTLINE

PAD LAYOUT DETAILS



Controlling dimensions are in millimeters. Approximate conversions are given in inches

PACKAGE DIMENSIONS

DIM	Millin	neters	Inc	hes	DIM	Millimeters		Inches	
DIIVI	Min	Max	Min	Max	DIIVI	Min	Max	Min	Max
Α	1.40	1.60	0.550	0.630	е	1.40	1.50	0.055	0.059
b	0.38	0.48	0.015	0.019	Е	3.75	4.25	0.150	0.167
b1	-	0.53	-	0.021	E1	-	2.60	-	0.102
b2	1.50	1.80	0.060	0.071	G	2.90	3.00	0.114	0.118
С	0.28	0.44	0.011	0.017	Н	2.60	2.85	0.102	0.112
D	4.40	4.60	0.173	0.181	-	-	-	-	-

© Zetex Semiconductors plc 2005

Europe	Americas	Asia Pacific	Corporate Headquarters
Zetex GmbH	Zetex Inc	Zetex (Asia) Ltd	Zetex Semiconductors plc
Streitfeldstraße 19	700 Veterans Memorial Hwy	3701-04 Metroplaza Tower 1	Zetex Technology Park
D-81673 München	Hauppauge, NY 11788	Hing Fong Road, Kwai Fong	Chadderton, Oldham, OL9 9LL
Germany	USA	Hong Kong	United Kingdom
Telefon: (49) 89 45 49 49 0	Telephone: (1) 631 360 2222	Telephone: (852) 26100 611	Telephone (44) 161 622 4444
Fax: (49) 89 45 49 49 49	Fax: (1) 631 360 8222	Fax: (852) 24250 494	Fax: (44) 161 622 4446
europe.sales@zetex.com	usa.sales@zetex.com	asia.sales@zetex.com	hq@zetex.com

These offices are supported by agents and distributors in major countries world-wide.

This publication is issued to provide outline information only which (unless agreed by the Company in writing) may not be used, applied or reproduced for any purpose or form part of any order or contract or be regarded as a representation relating to the products or services concerned. The Company reserves the right to alter without notice the specification, design, price or conditions of supply of any product or service.

For the latest product information, log on to $\underline{www.zetex.com}$

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Diodes Inc.: ZXTP2008ZTA